



### 20V N-Channel Enhancement Mode MOSFET

Voltage 20 V Current 950mA

#### **Features**

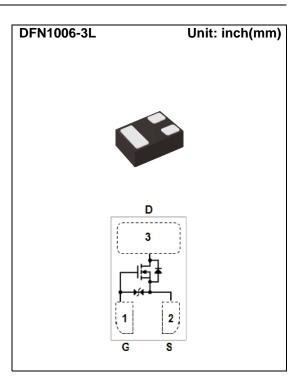
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN1006-3L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.00002 ounces, 0.0007 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETI	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V <sub>DS</sub>	20	V	
Gate-Source Voltage	V <sub>G</sub> s	<u>+</u> 8			
Continuous Drain Current (Note 4)		I <sub>D</sub>	950	mA	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	1900		
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	500	mW	
	Derate above 25°C		4	mW/°C	
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	°C	
Typical Thermal resistance - Junction to Ambient (Note 3,4)		Reja	250	°C/W	

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.3	0.5	1			
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA	-	220	300	mΩ		
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =400mA	-	250	400			
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =200mA	-	300	550			
		V <sub>GS</sub> =1.5V, I <sub>D</sub> =100mA	-	340	800			
		V <sub>GS</sub> =1.2V, I <sub>D</sub> =100mA	-	480	1500			
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA		
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10			
Dynamic (Note 5)								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V (Note 2)	-	1.1	-	nC		
Gate-Source Charge	$Q_{gs}$		-	0.16	-			
Gate-Drain Charge	$Q_{gd}$		-	0.12	-			
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHZ	-	46	-	pF		
Output Capacitance	Coss		-	15	-			
Reverse Transfer Capacitance	Crss		-	3	-			
Turn-On Delay Time	td <sub>(on)</sub>	\/ 40\/   500 ··· A	-	5.3	-	ns		
Turn-On Rise Time	tr	$V_{DD}$ =10V, $I_{D}$ =500mA, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ (Note 2)	-	22	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	43	-			
Turn-Off Fall Time	tf		-	31	-			
Drain-Source Diode								
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	500	mA		
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V	-	0.7	1	V		

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

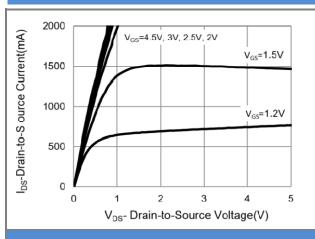
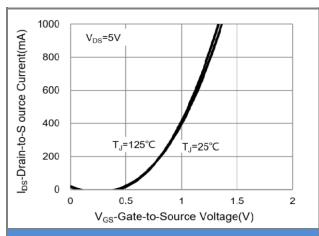


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

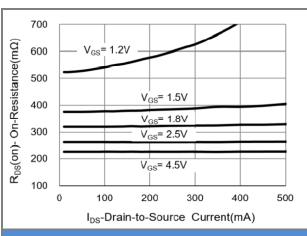


Fig.3 On-Resistance vs. Drain Current

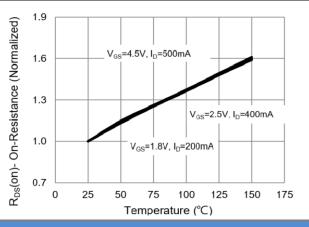


Fig.4 On-Resistance vs. Junction temperature

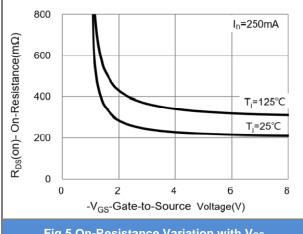
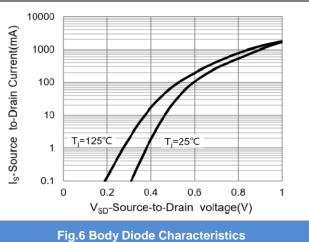


Fig.5 On-Resistance Variation with V<sub>GS</sub>







### **TYPICAL CHARACTERISTIC CURVES**

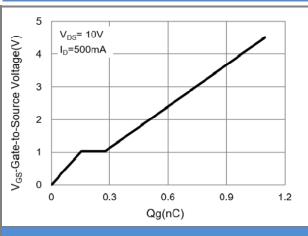


Fig.7 Gate-Charge Characteristics

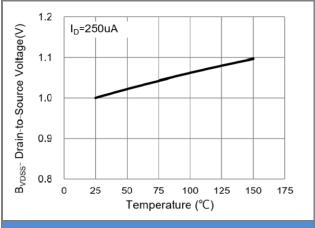


Fig.8 Breakdown Voltage Variation vs. Temperature

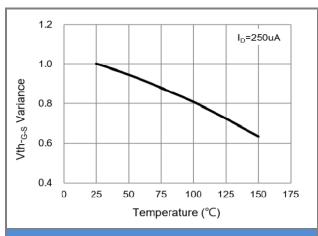


Fig.9 Threshold Voltage Variation with Temperature

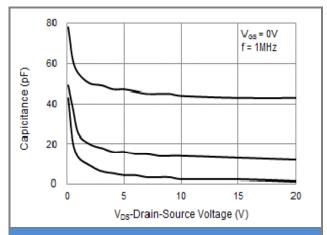


Fig.10 Capacitance vs. Drain-Source Voltage

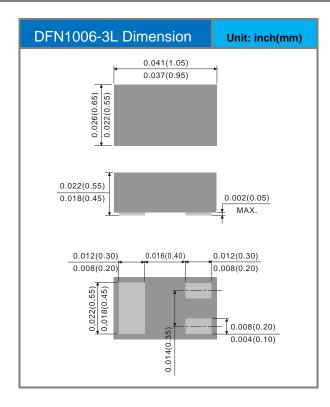


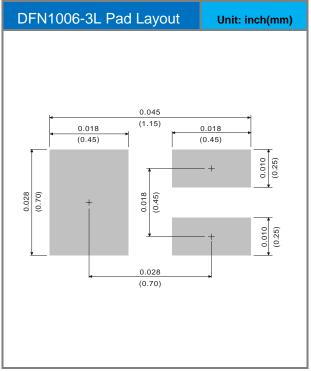


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ1916_R1_00001	DFN1006-3L	10K pcs / 7" reel	G	Halogen free

## **Packaging Information & Mounting Pad Layout**









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